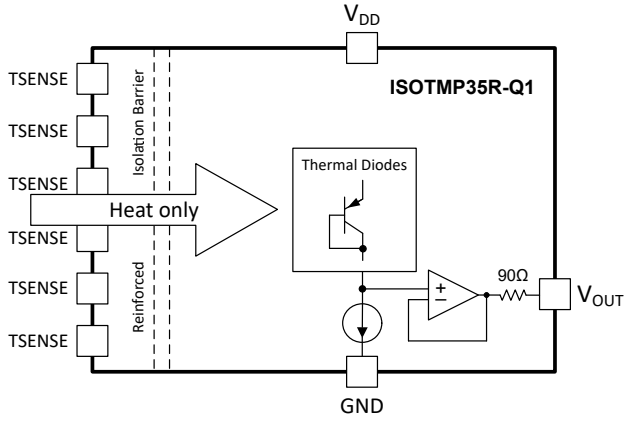
ISOTMP35R-Q1 Automotive ±2.5°C, 5kV$_{RMS}$ Reinforced Isolated Temperature Sensor with Analog Output and 1.06kV$_{RMS}$ Working Voltage

1 Features

- AEC-Q100 qualified with:
  - Temperature grade 0: –40°C to 150°C T_A
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C5
- Functional Safety-Capable
  - Documentation available to aid functional safety system design
- Robust integrated isolation barrier:
  - Withstand isolation voltage: 5kV$_{RMS}$
  - Isolation working voltage: 1.06kV$_{RMS}$
- Isolation barrier life: >30 years
- Temperature sensor accuracy:
  - ±0.5°C typical at 25°C
  - ±2.5°C maximum from 0°C to 70°C
  - ±3.5°C maximum from –40°C to 150°C
- Operating supply range: 3V to 34V
- Positive slope sensor gain: 10mV/°C
- Sensor offset: 500mV at 0°C
- Fast thermal response: <4s
- Short circuit protected output
- Low power consumption: 45µA (typical)
- Safety-related certifications (planned):
  - 5kV$_{RMS}$ isolation for 1 minute per UL 1577

2 Applications

- HEV/EV battery-management system (BMS)
- HEV/EV on-board and wireless charger
- HEV/EV DC/DC converter
- HEV/EV inverter and motor control
- Powertrain temperature sensor
- SiC PowerFET temperature monitoring
- IGBT PowerFET temperature monitoring



Functional Block Diagram

3 Description

The ISOTMP35R-Q1 is the industry's first reinforced isolated temperature sensor IC, combining an integrated isolation barrier, up to 5kV$_{RMS}$ withstand voltage, with an analog temperature sensor featuring a 10mV/°C slope from –40°C to 150°C. This integration enables the sensor to be co-located with high-voltage heat sources (for example: HV FETs, IGBTs, or HV contactors) without requiring expensive isolation circuitry. The direct contact with the high-voltage heat source also provides greater accuracy and faster thermal response compared with approaches where the sensor is placed further away to meet isolation requirements.

Operating from a non-isolated 3V to 34V supply, the ISOTMP35R-Q1 allows easy integration into applications where subregulated power is not available on the high-voltage plane.

The best output voltage of the ISOTMP35R-Q1 ranges from 100mV to 2V for a –40°C to 150°C temperature range. The ISOTMP35R-Q1 does not require any external calibration or trimming to provide a worst-case accuracy of ±0.5°C at room temperature and ±3.5°C over the full –40°C to 150°C temperature range. The linear output, 500mV offset, and factory calibration of the ISOTMP35R-Q1 simplify the circuitry requirements in a single supply environment where reading negative temperatures is necessary.

The integrated isolation barrier satisfies UL 1577 requirements. The surface mount package (12-pin SSOP) provides excellent heat flow from the heat source to the embedded thermal sensor, minimizing thermal mass and providing more accurate heat-source measurement. This reduces the need for time-consuming thermal modeling and improves system design margin by reducing mechanical variations due to manufacturing and assembly.

Packaging Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)
ISOTMP35R-Q1	DFP (SSOP, 12)	10.3mm × 3.6mm

(1) For more information, see Section 10.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.

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4 Pin Configuration and Functions

Figure 4-1. DFP Package 12-Pin SSOP Top View

Table 4-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	DFP		
GND	5	G	Ground
NC	2	—	No connect
	4		
	6		
TSENSE	7	—	Temperature pin connected to high-voltage heat source
	8		
	9		
	10		
	11		
	12		
V_{DD}	1	P	Supply voltage
V_{OUT}	3	O	Output voltage proportional to temperature

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power

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5 Specifications

5.1 Absolute Maximum Ratings

Over free-air temperature range unless otherwise noted(1)

		MIN	MAX	UNIT
Supply voltage	V_{DD} to GND	–0.3	36	V
Output voltage	V_{OUT} to GND	–0.3	V_{DD} + 0.3 (2)	V
Output current	I_{OUT}	–10	10	mA
Temperature	Operating junction temperature, T_J	–60	155	°C
	Storage temperature, T_{stg}	–65	155	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) Maximum voltage must not exceed 36V.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002(1) HBM ESD Classification Level 2	±2500	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C5	±1000	

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

		MIN	NOM	MAX	UNIT
V_{DD}	Supply voltage	3		34	V
T_A	Operating ambient temperature	–40		150	°C

5.4 Thermal Information

THERMAL METRIC(1)		ISOTMP35R-Q1 DFP (SSOP) 12 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	99.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	127.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	—	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	74.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	92.6	°C/W
ψ_{JB}	Junction-to-board characterization parameter	73.4	°C/W
M_T	Thermal Mass	TBD	mJ/°C

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

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5.5 Insulation Specification

Over free-air temperature range and V_{DD} = 3V to 34V (unless otherwise noted)
Typical specifications are at T_A = 25°C and V_{DD} = 3.3V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	VALUE	UNIT
GENERAL				
CLR	External Clearance(1)	Shortest terminal-to-terminal distance through air	>8	mm
CPG	External Creepage(1)	Shortest terminal-to-terminal distance across the package surface	>8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	17	µm
CTI	Comparative tracking index	DIN EN 60112; IEC 60112	>600	V
V_{DC}	Maximum isolation DC voltage	DC voltage	1500	V_{DC}
	Material Group	According to IEC 60664-1	I	
	Overvoltage category	Rated mains voltage ≤ 150V_{RMS}	I-IV	
		Rated mains voltage ≤ 300V_{RMS}	I-III	
V_{IORM}	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	1500	V_{PK}
V_{IOWM}	Maximum isolation working voltage	AC voltage (sine wave), time-dependent dielectric breakdown (TDDB) test	1060	V_{RMS}
V_{IOTM}	Maximum transient isolation voltage	V_{TEST} = V_{IOTM}, t = 60s (qualification test), V_{TEST} = 1.2 × V_{IOTM}, t = 1s (100% production test)	7000	V_{PK}
V_{IMP}	Maximum impulse voltage(2)	Tested in air, 1.2/50µs waveform per IEC 62368-1(5)	8000	V_{PK}
V_{IOSM}	Maximum surge isolation voltage(3)	Tested in oil (qualification test), 1.2/50µs waveform per IEC 62368-1(5)	10400	V_{PK}
q_{pd}	Apparent charge(4)	Method a, after input/output safety test subgroups 2 and 3, $V_{pd(ini)}$ = V_{IOTM}, t_{ini} = 60s, $V_{pd(m)}$ = 1.2 × V_{IORM}, t_m = 10s	≤5	pC
		Method a, after environmental tests subgroup 1, $V_{pd(ini)}$ = V_{IOTM}, t_{ini} = 60s, $V_{pd(m)}$ = 1.3 × V_{IORM}, t_m = 10s	≤5	
		Method b, at preconditioning (type test) and routine test, $V_{pd(ini)}$ = V_{IOTM}, t_{ini} = 1s, $V_{pd(m)}$ = 1.5 × V_{IORM}, t_m = 1s	≤5	
C_{IO}	Barrier capacitance, input to output(5)	V_{IO} = 0.1V_{PP} at 100kHz	TBD	pF
R_{IO}	Insulation resistance, input to output(5)	V_{IO} = 500V at T_A = 25°C	$>10^{12}$	Ω
		V_{IO} = 500V at 100°C ≤ T_A ≤ 125°C	$>10^{11}$	
		V_{IO} = 500V at T_A = 150°C	$>10^{9}$	
	Pollution degree		2	
	Climatic category		55/125/21	
UL 1577				
V_{ISO}	Withstand isolation voltage	V_{TEST} = V_{ISO}, t = 60s (qualification); V_{TEST} = 1.2 × V_{ISO}, t = 1s (100% production)	5000	V_{RMS}

(1) Apply creepage and clearance requirements according to the specific equipment isolation standards of an application. Take care to maintain the creepage and clearance distance of the board design to make sure that the mounting pads of the isolator on the printed circuit board do not reduce this distance. Creepage and clearance on a printed circuit board become equal in certain cases. Techniques such as inserting grooves, ribs, or both on a printed circuit board are used to help increase these specifications.
(2) Testing is carried out in air to determine the surge immunity of the package.
(3) Testing is carried out in oil to determine the intrinsic surge immunity of the isolation barrier.
(4) Apparent charge is electrical discharge caused by a partial discharge (pd).
(5) All pins on each side of the barrier tied together creating a two-terminal device.

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5.6 Power Ratings

V_{DD} = 34V, T_A = 125℃, T_J = 150℃, device soldered on the device evaluation board.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_D	Maximum power dissipation	V_{DD} = 34V, I_Q = 140µA, no load at V_{OUT}			TBD	µW

5.7 Safety-Related Certifications

UL	
UL 1577 Component Recognition Program	Certified according to IEC 62368-1 CB
File number: Pending	Certificate number: Pending

5.8 Safety Limiting Values

Safety limiting(1) intends to minimize potential damage to the isolation barrier upon failure of input or output circuitry.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_S	Safety input, output, or supply current	$R_{\theta JA}$ = 99.5°C/W, V_I = 5V, T_J = 150°C, T_A = 25°C			TBD	mA
P_S	Safety input, output, or total power	$R_{\theta JA}$ = 99.5°C/W, T_J = 150°C, T_A = 25°C			TBD	W
T_S	Maximum safety temperature				150	℃

(1) The maximum safety temperature, T_S, has the same value as the maximum junction temperature, T_J, specified for the device. The I_S and P_S parameters represent the safety current and safety power, respectively. The maximum limits of I_S and P_S should not be exceeded. These limits vary with the ambient temperature, T_A.
The junction-to-air thermal resistance, $R_{\theta JA}$, in the *Thermal Information* table is that of a device installed on a device evaluation board. Use these equations to calculate the value for each parameter:
$T_J = T_A + R_{\theta JA} \times P$, where P is the power dissipated in the device.
$T_{J(max)} = T_S = T_A + R_{\theta JA} \times P_S$, where $T_{J(max)}$ is the maximum allowed junction temperature.
$P_S = I_S \times V_I$, where V_I is the maximum input voltage.

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5.9 Electrical Characteristics

Over free-air temperature range and V_{DD} = 3V to 34V (unless otherwise noted)
Typical specifications are at T_A = 25°C and V_{DD} = 3.3V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
TEMPERATURE SENSOR							
T_{ERR}	Temperature accuracy	T_A = 25°C, V_{DD} = 3.3V			±0.5		°C
		T_A = 0°C to 70°C		–2.5		2.5	
		T_A = –40°C to 150°C		–3.5		3.5	
T_{LTD}	Long-term stability and drift(1)	300 hours at 150°C			TBD		°C
T_{GAIN}	Sensor sensitivity (gain)	T_A = –40°C to 150°C			10		mV/°C
V_{OUT}	Output voltage	T_A = 0°C			500		mV
		T_A = 25°C			750		
		T_A = 30°C			800		
T_{NL}	Output nonlinearity	T_A = –40°C to 150°C		–0.8		0.8	°C
t_{RESP_D}	Thermal response time (directional)	2-layer 62-mil Rigid PCB 2oz. Copper	$T_{63\%}$, T_{TSENSE} = 25°C to 75°C T_{PIN1-6} = 25°C		3.75		s
t_{RESP_L}	Thermal response time (stirred liquid)	0.5in × 0.5in, 2-layer 62-mil PCB	$T_{63\%}$, T_{STEP} = 25°C to 150°C		2.01		
t_{RESP_A}	Thermal response time (still air)	0.5in × 0.5in, 2-layer 62-mil PCB	$T_{63\%}$, T_{STEP} = 25°C to 150°C		TBD		
ANALOG OUTPUT							
V_{OUTR}	Output voltage range	T_A = –40°C to 150°C		0.1		2	V
Z_{OUT}	Output impedance	I_{LOAD} = 0µA to 100µA, f = 0Hz to 1000Hz			90		Ω
I_{OUT}	Operating output current	V_{OUT} source current				100	µA
		V_{OUT} sink current				1	
I_{OUT-SC}	Output short-circuit current limit	V_{OUT} short-circuit source current			750	TBD	µA
		V_{OUT} short-circuit sink current			60	TBD	µA
CMTI	Common-mode transient immunity	V_{DD} = 5V, V_{CM} = 750V, t_{PULSE} = 10µs C_{LOAD} = 100nF, R_{LOAD} = 15kΩ, ΔV_{OUT} < 200mV			65.8		kV/µs
REG_{LI}	Line regulation	3V ≤ V_{DD} ≤ 34V		–1.2		1.2	mV/V
REG_{LD}	Load regulation	I_{LOAD} = 0µA to 100µA			9		mV
C_{LOAD}	Capacitive load drive	R_{ISO} = 0Ω				220	nF
		R_{ISO} = 500Ω				TBD	nF
		R_{ISO} = 1000Ω				TBD	nF
POWER SUPPLY							
I_Q	Quiescent current	T_A = 25°C, V_{DD} = 3.3V			45	65	µA
		T_A = –40°C to 150°C				140	µA
V_{ON-TH}	Turn-on threshold voltage	T_A = –40°C to 150°C			2.1	2.8	V
V_{OFF-TH}	Turn-off threshold voltage	T_A = –40°C to 150°C		1.7	2.1		V
t_{ON}	Turn-on time	C_{LOAD} = 0pF			25		µs
PSRR	Power supply rejection ratio	T_A = 25°C, V_{DD} = 3.3V, f = 1000Hz			–75		dB

(1) Long-term stability and drift is determined using accelerated operational life testing at a junction temperature of 150°C.

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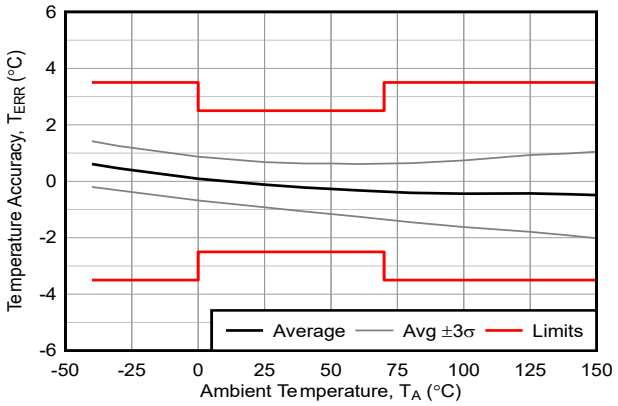
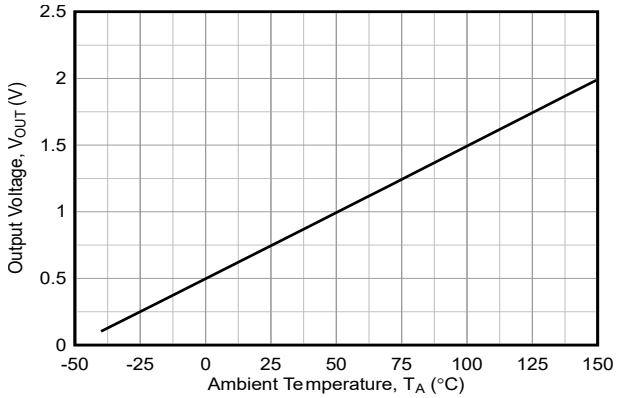
5.10 Typical Characteristics

at T_A = 25°C (unless otherwise noted)



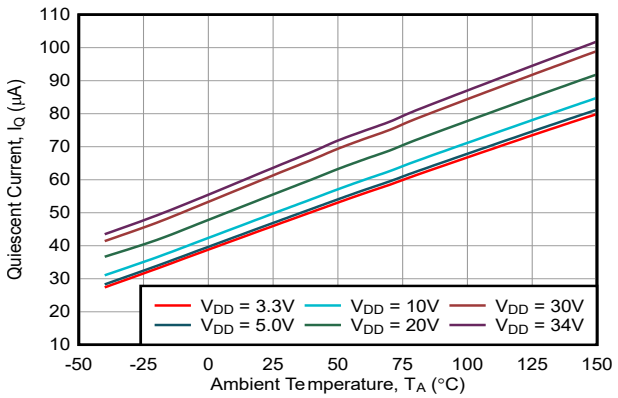
V_{DD} = 3.3V, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-1. Accuracy vs Ambient Temperature



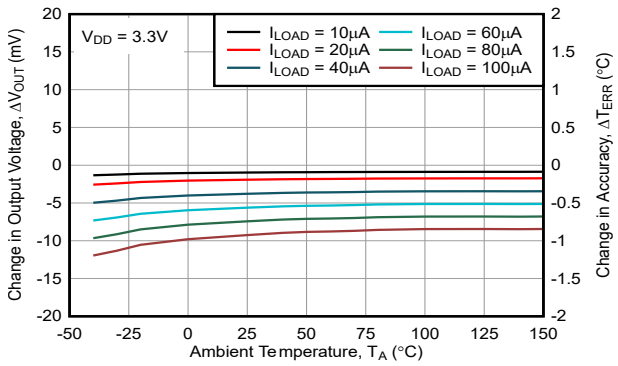
V_{DD} = 3 to 34V, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-2. V_{OUT} vs Ambient Temperature



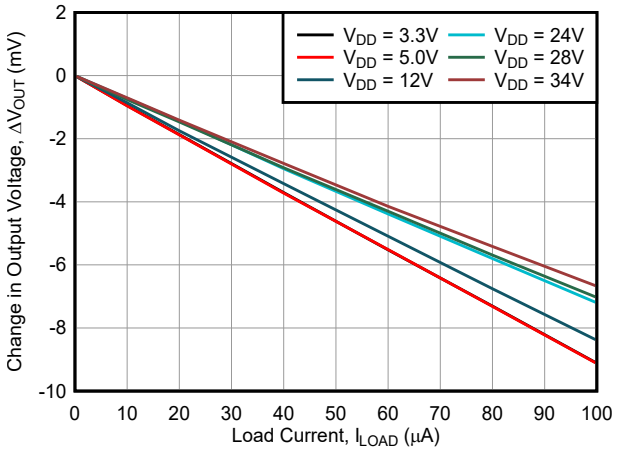
I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-3. Supply Current vs Ambient Temperature



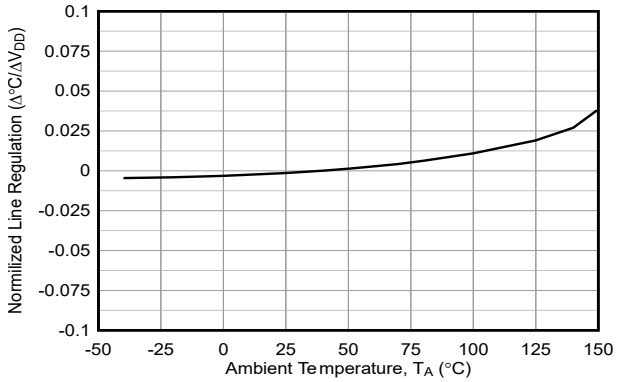
V_{DD} = 3.3V, C_{LOAD} = 0pF

Figure 5-4. Load Regulation vs Ambient Temperature



T_A = 25°C, C_{LOAD} = 0pF

Figure 5-5. Output Voltage vs Load Current



V_{DD} = 3 to 34V, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-6. Line Regulation (Δ°C / ΔV_{DD}) vs Ambient Temperature

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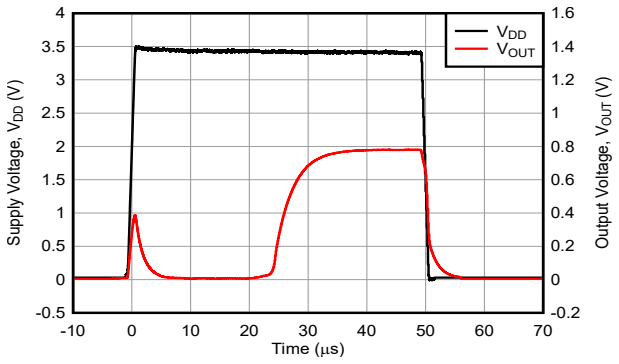
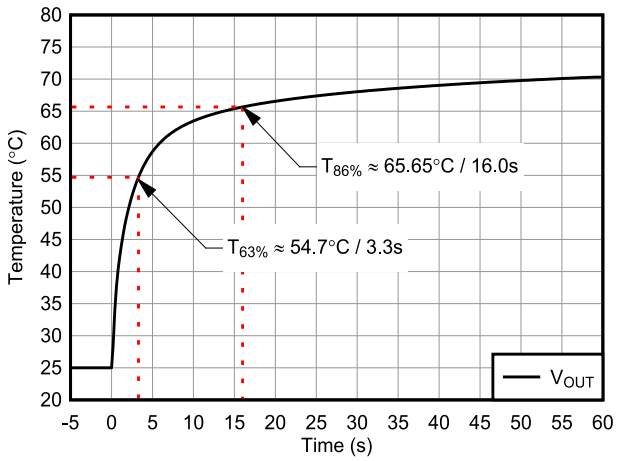


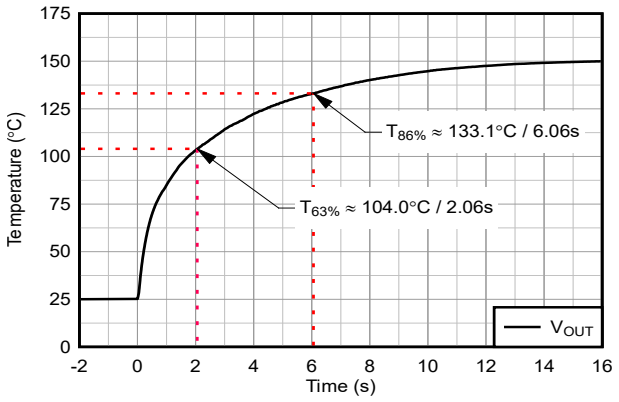
I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-7. Output vs Settling Time to V_{DD} Step



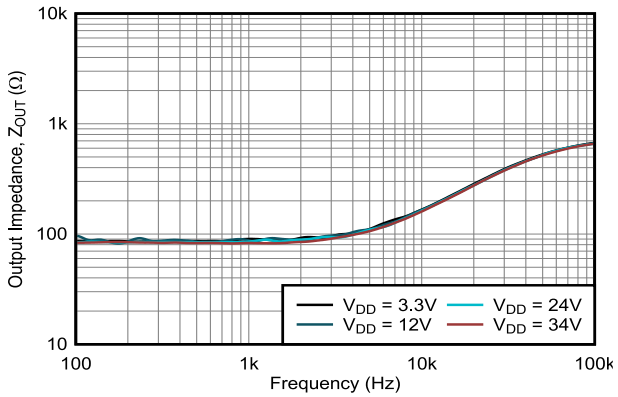
TSENSE = 25°C to 72°C, T_{PIN1-6} = 25°C
(2-layer 62-mil rigid PCB, 2oz copper)

Figure 5-8. Thermal Response (Directional)



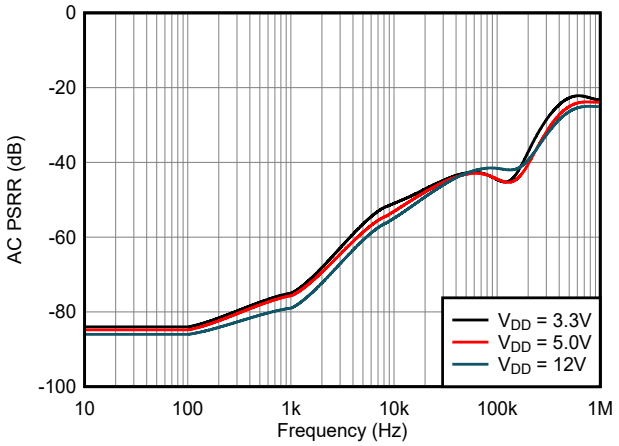
Air 25°C to Fluid Bath 150°C, 0.5 × 0.5 inch PCB

Figure 5-9. Thermal Response (Air-to-Fluid Bath)



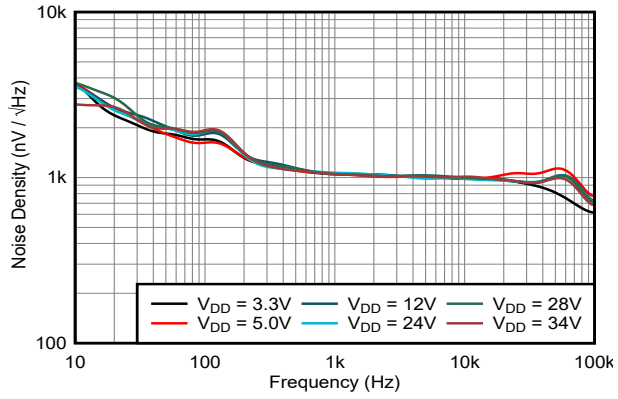
T_A = 25°C, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-10. Output Impedance vs Frequency



T_A = 25°C, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-11. Power Supply Rejection Ratio vs Frequency



T_A = 25°C, I_{LOAD} = 0µA, C_{LOAD} = 0pF

Figure 5-12. Output Noise Density

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6 Detailed Description

6.1 Overview

The ISOTMP35R-Q1 is a linear analog output temperature sensor with an output voltage proportional to temperature. The temperature sensor has an accuracy of ±2.5°C from 0°C to 70°C and ±3.5°C over the full temperature range of –40°C to 150°C. The ISOTMP35R-Q1 provides a positive slope output of 10mV/°C over the full –40°C to 150°C and a supply range from 3V to 34V. A class-A output driver provides a maximum output current of 100µA to drive capacitive loads up to 220nF.

6.2 Functional Block Diagram

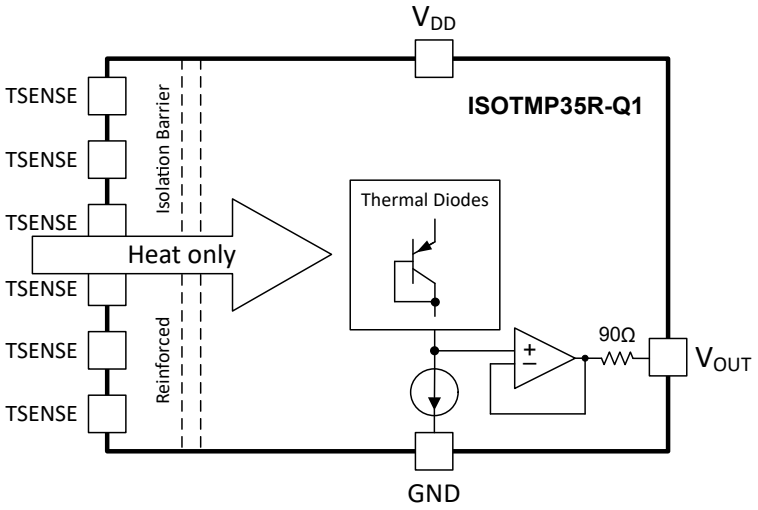

Figure 6-1. Functional Block Diagram

6.3 Features Description

The ISOTMP35R-Q1 device combines a robust integrated isolation barrier with a tight accuracy analog output temperature sensor. All the features related to the analog output, accuracy, output characteristics of the sensor, and drive characteristics of the output are discussed in the analog output section.

6.3.1 Integrated Isolation Barrier and Thermal Response

The ISOTMP35R-Q1 is designed to integrate a robust isolation barrier while maximizing the heat flow of a local heat source. This is made possible by an SSOP-12 package designed to provide a $5kV_{RMS}$ isolating rating (UL 1577) along with an isolation mechanism that minimizes thermal response from the TSENSE pins to the temperature sensor.

6.3.2 Analog Output

The analog output of the ISOTMP35R-Q1 has several characteristics, such as the output accuracy, linearity, and drive capability, that must be understood to design the interface to the rest of the signal chain.

6.3.2.1 Output Accuracy

As illustrated in Figure 5-2, the ISOTMP35R-Q1 device's output is linear with a 500mV offset voltage and a temperature coefficient or sensor gain of 10mV/°C. The ISOTMP35R-Q1, therefore, adheres to a simple transfer function given as

$$V_{OUT} = (10mV/°C \times T_A) + 500mV \quad (1)$$

where

- T_A is the Ambient Temperature in °C.

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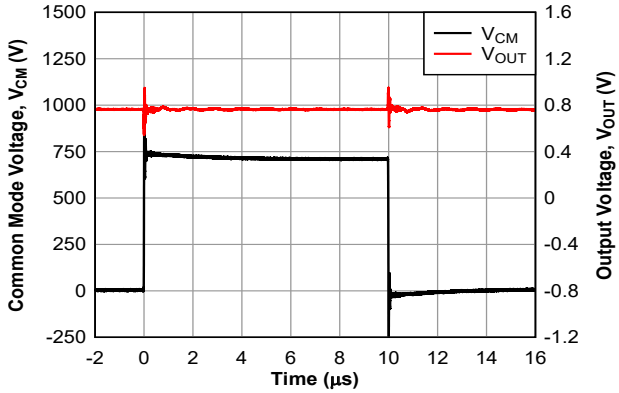
6.3.2.2 Drive Capability

A class-A output driver provides a maximum output of 100µA to drive capacitive loads up to 220nF, while sinking less than 1µA. However, for the best accuracy, load current can be minimized to prevent self-heating contributions to the total error.

6.3.2.3 Common Mode Transient Immunity (CMTI)

CMTI is the device's capability to tolerate a rising or falling voltage step on the high-voltage pins without coupling a significant disturbance to the output signal. The ISOTMP35R-Q1 device is specified for the maximum common-mode transition rate under which the output signal does not experience a disturbance greater than 200mV lasting longer than 4µs, as shown in Figure 6-2 with a 65.8kV/µs common-mode input step. Higher edge rates than the specified CMTI can be supported with sufficient blanking time after common-mode transitions.



T_A = 25°C, V_{DD} = 5.0V, V_{CM} = 750V, R_{LOAD} = 15kΩ, C_{LOAD} = 100nF

Figure 6-2. Common-Mode Transient Response

6.3.3 Thermal Response

The SSOP-12 package is designed to maximize the heat flow and minimize the thermal response time from the TSENSE pins to the temperature sensor, while also providing the 5kV_{RMS} isolation rating (UL 1577).

When evaluating thermal response with a thermal contact device, take care to understand the gradient established by the heat source in the application. Traditionally, most temperature sensors are characterized on the basis of a "stirred-liquid" thermal response test, which sees the totality of the device submerged into a circulated oil bath at an elevated temperature, which typically provides the best possible response the device yields, having all parts of the device held to the secondary temperature for the purposes of establishing a new thermal equilibrium point. This style of test is visualized in Stirred Liquid Thermal Response Test, and the results of this test are presented in Thermal Response (Air-to-Fluid Bath).

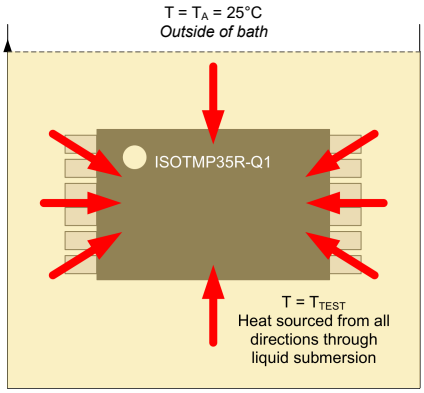


Figure 6-3. Stirred Liquid Thermal Response Test

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The ISOTMP35R-Q1 device is also evaluated by means of a "directional" temperature response test, where only the thermally connected, high-voltage pins of the device are exposed to the elevated temperature, while the remaining low-voltage pins remain in free air at a standard room temperature condition of 25°C. The objective of this form of thermal response test is to more properly evaluate the thermal conductivity of the device under test, even though a slight error can persist from the reference temperature.

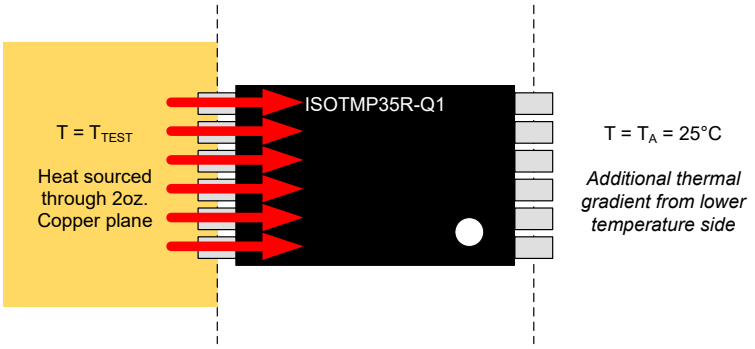

Figure 6-4. Directional Thermal Response Test

This is demonstrated in Figure 6-5, where ISOTMP35R-Q1 is shown alongside a standard negative temperature coefficient (NTC) thermistor, as well as the same NTC adhered via non-conductive thermal epoxy to the high voltage copper, placed at a clearance distance of 8mm from the temperature source. The resulting responses demonstrate the excellent response time as well as the accuracy of the ISOTMP35R-Q1 device. The reference temperature in this test is 75°C.

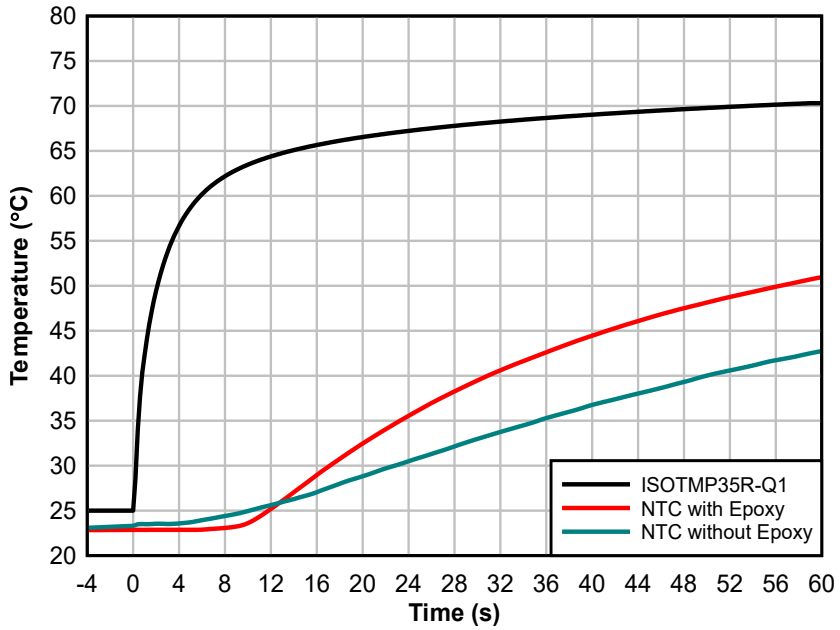

Figure 6-5. ISOTMP35R-Q1 Directional Thermal Response

6.4 Device Functional Modes

The singular functional mode of the ISOTMP35R-Q1 is an analog output directly proportional to temperature.

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7 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The ISOTMP35R-Q1 device offers versatile features designed for a wide range of high-voltage temperature-sensing applications. The ISOTMP35R-Q1 operates from a supply voltage as low as 3V with a typical current consumption of only 45µA. This low-power capability makes the ISOTMP35R-Q1 device well suited for battery-powered systems, including applications where multiple cells are stacked to generate high output voltages.

7.1.1 External Buffer

In case of higher capacitance on the output or a long trace between the sensor and the ADC, an external buffer can be added. This implementation is shown in Figure 7-1 for the signal to be a temperature voltage to be sent through a differential pair.

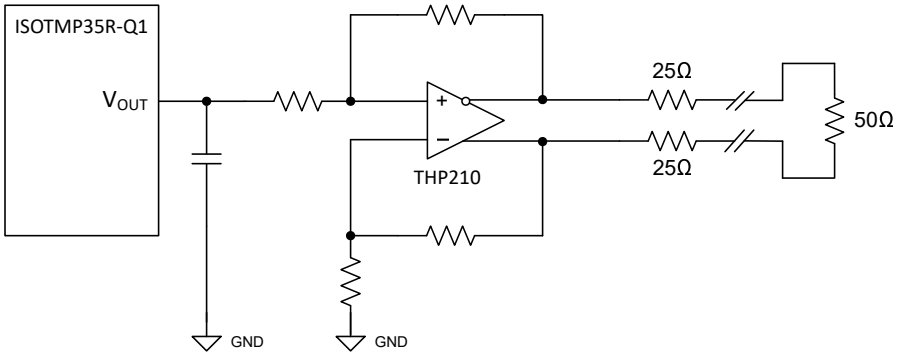

Figure 7-1. Buffered Differential Pair Data Transmission

7.1.2 ADC Interface Considerations

The ISOTMP35R-Q1 device provides an analog voltage output (V_{OUT}) that can be digitized using an external analog-to-digital converter (ADC). To ensure accurate temperature measurements, TI recommends using an ADC with at least 12-bit resolution. With a 2.5V reference, a 12-bit ADC provides an LSB of approximately 0.61mV, corresponding to a temperature resolution of 0.061°C per LSB. This resolution is sufficient for most applications requiring precise temperature monitoring.

When interfacing the ISOTMP35R-Q1 device with an ADC, additional circuitry is recommended to ensure signal integrity:

- C_{LOAD} capacitor: Stabilizes V_{OUT} and reduces ripples caused by high-voltage transients across the isolation barrier, and should be placed close to the ISOTMP35R-Q1 V_{OUT} pin.
- RC filter (R_{FILTER}, C_{FILTER}): Suppresses noise on the V_{OUT} line and should be placed close to the ADC input.
- C_{FILTER} capacitor: Also acts as a charge reservoir to mitigate voltage glitches during ADC sampling.

Figure 7-2 illustrates a recommended circuit for connecting the ISOTMP35R-Q1 output to an ADC. This configuration ensures accurate digitization of the ISOTMP35R-Q1 output with minimal noise and transient effects.

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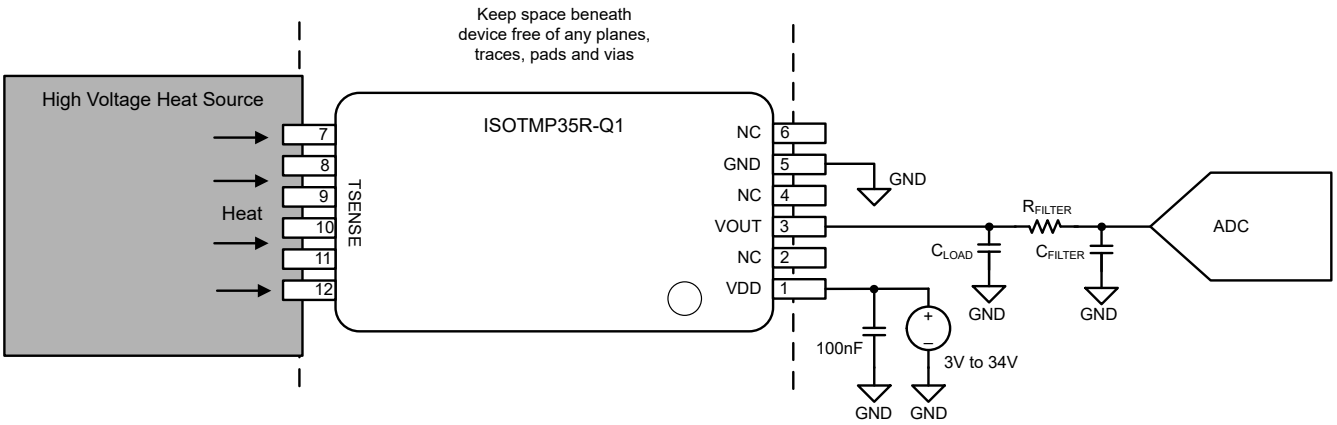

Figure 7-2. Connecting the ISOTMP35R-Q1 Output to an ADC

7.1.3 Electromagnetic Noise Mitigation

The ISOTMP35R-Q1 device is designed to connect to high-voltage heat sources, including switching MOSFETs. These devices often generate electromagnetic interference (EMI) and noise that can couple into the ISOTMP35R-Q1 output (V_{OUT}). If not properly filtered, this noise can cause large temperature accuracy errors. Effective EMI mitigation is therefore critical to maximizing the accuracy and reliability of the ISOTMP35R-Q1 device.

7.1.3.1 Filtering Techniques

EMI mitigation begins at the schematic level. TI recommends using RC filters or Pi filters on ISOTMP35R-Q1 traces to attenuate coupled noise. In addition, ferrite beads on V_{DD} and GND help suppress high-frequency noise before the noise couples into the device.

Place filtering components both at the ISOTMP35R-Q1 pins and at the signal termination point. For example, placing an RC filter only near the device leaves the rest of the trace vulnerable to noise pickup. Figure 7-3 illustrates an example filter configuration for reducing EMI effects.

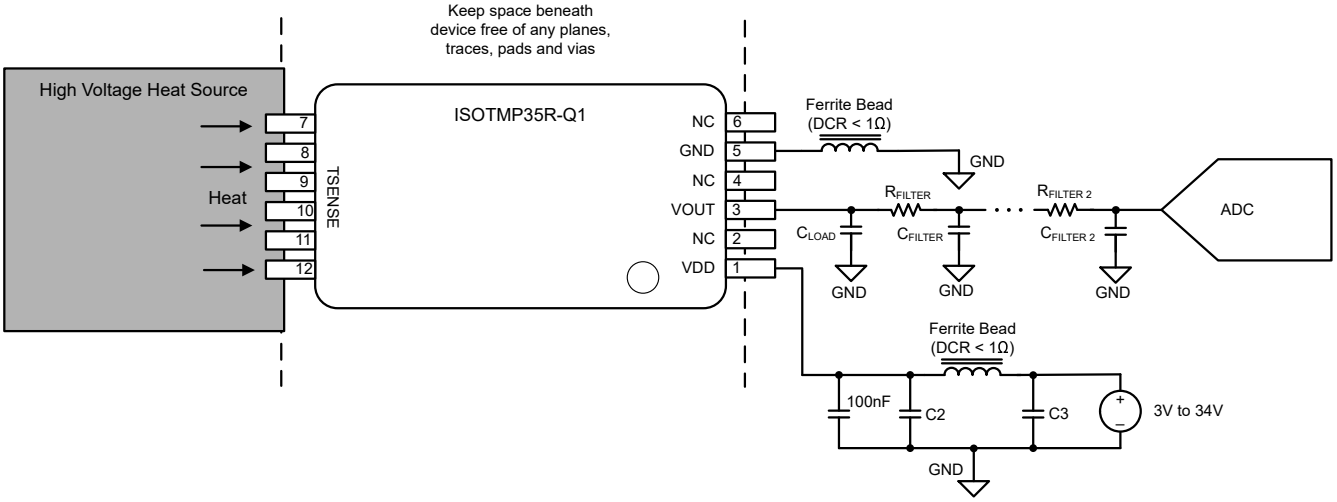

Figure 7-3. Example Filtering for EMI Mitigation

7.1.3.2 General Design Guidelines

While filter design depends on system-level noise sources, the following practices are recommended:

- Place a 0.1µF bypass capacitor as close as possible to the ISOTMP35R-Q1 V_{DD} pin. This capacitor is required for optimal operation and should always be present, even when additional filters are used.

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- Use C0G/NP0 capacitors for signal-path filtering, and limit SMT package size to 0603 or smaller to minimize parasitic effects.
- When selecting ferrite beads for high-frequency filtering, ensure DCR < 1Ω to avoid voltage drops that could introduce additional noise on V_{DD}.
- Use low-ESR capacitors, which provide a low-impedance path to ground and improve high-frequency noise suppression.

7.1.3.3 PCB Layout Practices

PCB layout also plays a key role in EMI performance:

- Route ISOTMP35R-Q1 signal traces away from high-voltage noise sources.
- Avoid wrapping traces around noisy components, which increases noise coupling.
- Where possible, route signal traces between quiet GND planes on two layers, using stitching vias to connect the planes. This provides a low-impedance return path for noise, reducing its effect on the signal.

By combining robust filtering with careful PCB layout, designers can significantly reduce EMI impact and ensure accurate temperature measurements.

7.1.4 Insulation Lifetime

Insulation lifetime projection data is collected by using the industry-standard time-dependent dielectric breakdown (TDDB) test method. In this test, all pins on each side of the barrier are tied together, creating a two-terminal device, and high voltage is applied between the two sides. See Figure 7-4 for TDDB test setup. The insulation breakdown data is collected at various high voltages, switching at 60Hz over temperature.

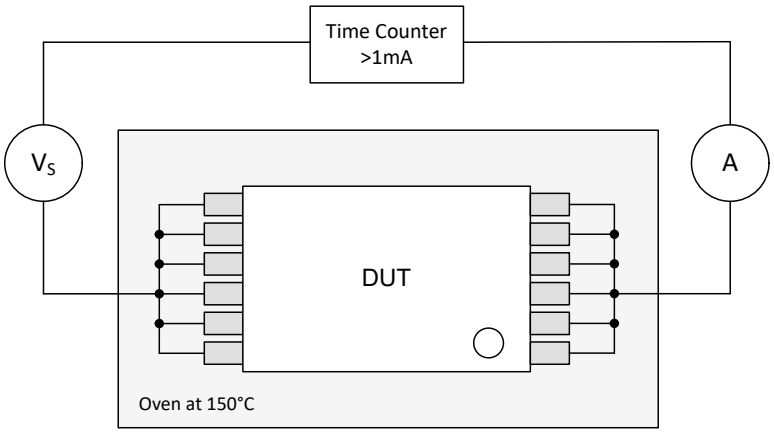

Figure 7-4. Test Setup for Insulation Lifetime Measurement

7.2 Power Supply Recommendations

To maintain stable operation, a 0.1µF ceramic bypass capacitor is recommended at the V_{DD} supply pin. This capacitor can be placed as close as possible to the device to provide effective noise decoupling. The ISOTMP35R-Q1 device operates from a single-supply configuration and does not require an isolated power source.

7.2.1 PSRR Considerations

Depending on the application, there can be a significant amount of high-frequency noise on the power supply line. If high-frequency noise (>100kHz) is present, the user can switch to a 1µF bypass capacitor to provide additional filtering on the power supply line. Increasing the bypass capacitance or choosing a capacitor with a lower ESR across frequency improves PSRR performance.

An additional power supply consideration is line regulation. For the ISOTMP35R-Q1 device, line regulation refers to the change in output temperature with changing power supply. Figure 5-6 shows that, across the entire

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environment temperature range, ISOTMP35R-Q1 maintains a steady amount change in temperature across V_{DD}.

7.3 Layout

7.3.1 Layout Guidelines

Voltage clearance on the line must be respected. A minimum of two layers is required for the ISOTMP35R-Q1 device. Standard layer stacking can be used for a 4-layer PCB where the signal traces can run either on the top or bottom layer. Solid ground and power plane must form the inner layer. See Figure 7-5 for a depiction of a plane and trace clearance under the device.

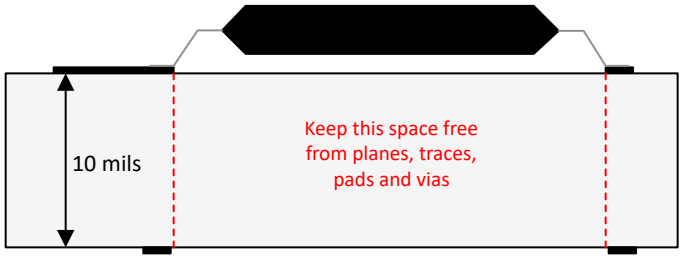

Figure 7-5. PCB Cross-Section

7.3.2 Layout Example

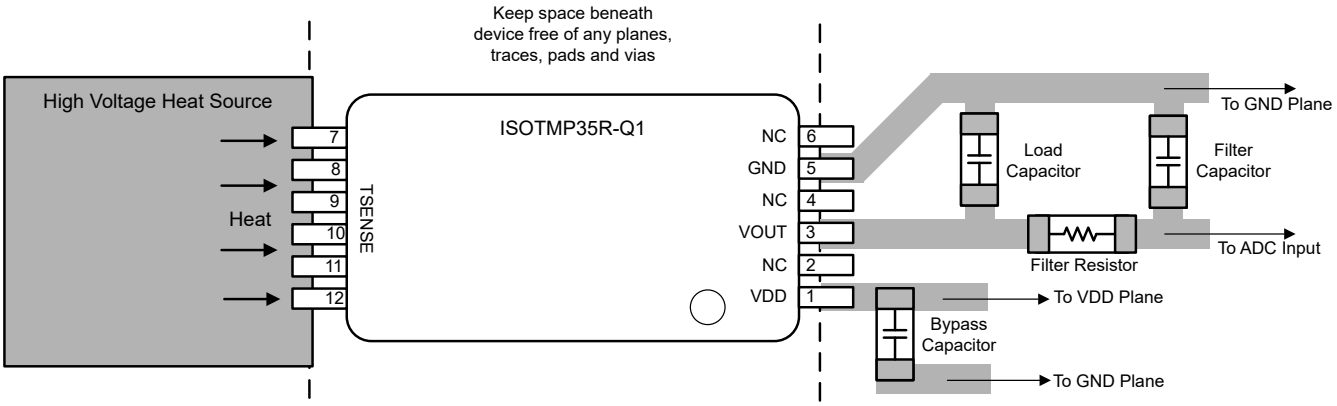

Figure 7-6. ISOTMP35R-Q1 Layout Example

8 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

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8.1 Documentation Support

8.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *ISOTMP35R Evaluation Module User's Guide*
- Texas Instruments, *Circuit for Driving an ADC with an Instrumentation Amplifier in High Gain*, circuit design
- Texas Instruments, *Driving a SAR ADC Directly Without a Front-End Buffer Circuit (Low-Power, Low-Sampling-Speed DAQ)*, circuit design

8.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

8.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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8.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

8.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from September 17, 2025 to December 30, 2025 (from Revision * (September 2025) to Revision A (December 2025))	Page
• Changed the status of this data sheet to Production Data	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
PISOTMP35REDFPRQ1	Active	Preproduction	SSOP (DFP) | 12	2000 | LARGE T&R	-	Call TI	Call TI	-40 to 150	

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF ISOTMP35R-Q1 :

- Catalog : ISOTMP35R

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

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